

1. General description

Hyperfast power diode in a TO252 (DPAK) plastic package.



2. Features and benefits

- Low leakage current
- Low thermal resistance
- Low reverse recovery current
- Reduces switching losses in associated MOSFET or IGBT

3. Applications

- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- Half-bridge/full-bridge switched-mode power supplies

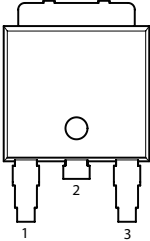
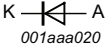
4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Notes | Values | | | Unit |
|-------------------------|-------------------------------------|---|-------|--------|------|------|------|
| Absolute maximum rating | | | | | | | |
| V _{RRM} | repetitive peak reverse voltage | | | 650 | | | V |
| I _{F(AV)} | average forward current | δ = 0.5 ; square-wave pulse; T _{mb} ≤ 128 °C; Fig. 1 ; Fig. 2 ; Fig. 3 | | 12 | | | A |
| I _{FRM} | repetitive peak forward current | δ = 0.5 ; t _p = 25 μs; T _{mb} ≤ 128 °C; square-wave pulse | | 24 | | | A |
| I _{FSM} | non-repetitive peak forward current | t _p = 10 ms; T _{j(init)} = 25 °C; sine-wave pulse; Fig. 4 | | 135 | | | A |
| | | t _p = 8.3 ms; T _{j(init)} = 25 °C; sine-wave pulse | | 148 | | | A |
| Symbol | Parameter | Conditions | Notes | Min | Typ | Max | Unit |
| Static characteristics | | | | | | | |
| V _F | forward voltage | I _F = 12 A; T _j = 25 °C; Fig. 6 | | - | 2.60 | 3.30 | V |
| | | I _F = 12 A; T _j = 150 °C; Fig. 6 | | - | 1.60 | 2.30 | V |
| Dynamic characteristics | | | | | | | |
| t _{rr} | reverse recovery time | I _F = 1 A; V _R = 30 V; dI _F /dt = 200 A/μs; T _j = 25 °C; Fig. 7 | | - | 13 | - | ns |

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------------------------------|--|---|
| 1 | n.c. | not connected |  |  |
| 2 | K | cathode [1] | | |
| 3 | A | anode | | |
| mb | K | mounting base; connected to cathode | | |

[1] It is not possible to connect to pin 2 of the TO252 package.

6. Ordering information

Table 3. Ordering information

| Type number | Package name | Orderable part number | Packing method | Small packing quantity | Package version | Package issue date |
|--------------|--------------|-----------------------|----------------|------------------------|-----------------|--------------------|
| BYC12MD-650P | TO252 | BYC12MD-650PJ | Reel | 2500 | TO252d | 07-Sep-2022 |

7. Marking

Table 4. Marking codes

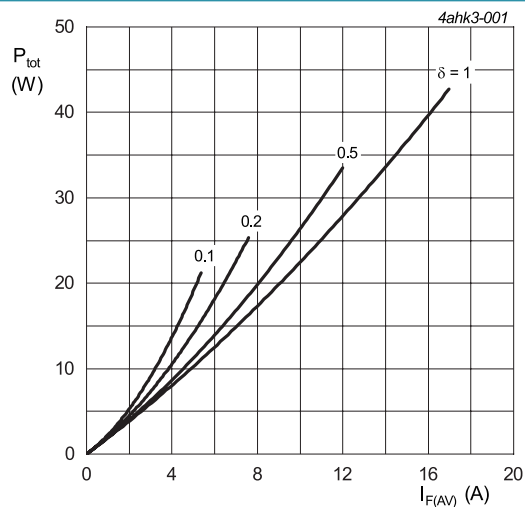
| Type number | Marking codes |
|--------------|-----------------|
| BYC12MD-650P | BYC12MD 650P |

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

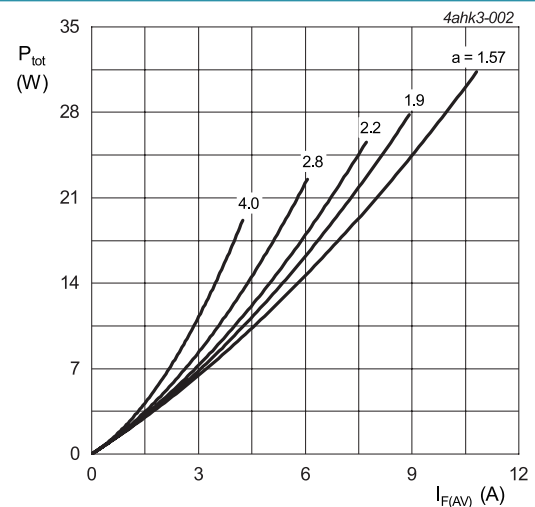
| Symbol | Parameter | Conditions | Notes | Values | Unit |
|-------------|-------------------------------------|--|-------|------------|--------------------|
| V_{RRM} | repetitive peak reverse voltage | | | 650 | V |
| V_{RWM} | crest working reverse voltage | | | 650 | V |
| V_R | reverse voltage | DC | | 650 | V |
| $I_{F(AV)}$ | average forward current | $\delta = 0.5$; square-wave pulse; $T_{mb} \leq 128\text{ }^{\circ}\text{C}$; Fig. 1 ; Fig. 2 ; Fig. 3 | | 12 | A |
| I_{FRM} | repetitive peak forward current | $\delta = 0.5$; $t_p = 25\text{ }\mu\text{s}$; $T_{mb} \leq 128\text{ }^{\circ}\text{C}$; square-wave pulse | | 24 | A |
| I_{FSM} | non-repetitive peak forward current | $t_p = 10\text{ ms}$; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$; sine-wave pulse; Fig. 4 | | 135 | A |
| | | $t_p = 8.3\text{ ms}$; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$; sine-wave pulse | | 148 | A |
| T_{stg} | storage temperature | | | -65 to 175 | $^{\circ}\text{C}$ |
| T_j | junction temperature | | | -65 to 175 | $^{\circ}\text{C}$ |



$$I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$$

$$V_o = 1.852\text{ V}; R_s = 0.0392\text{ }\Omega$$

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



$$a = \text{form factor} = I_{F(RMS)} / I_{F(AV)}$$

$$V_o = 1.852\text{ V}; R_s = 0.0392\text{ }\Omega$$

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

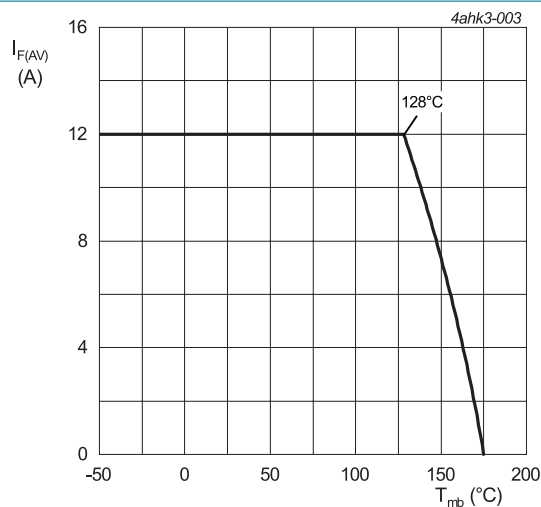


Fig. 3. Forward current as a function of mounting base temperature; maximum values

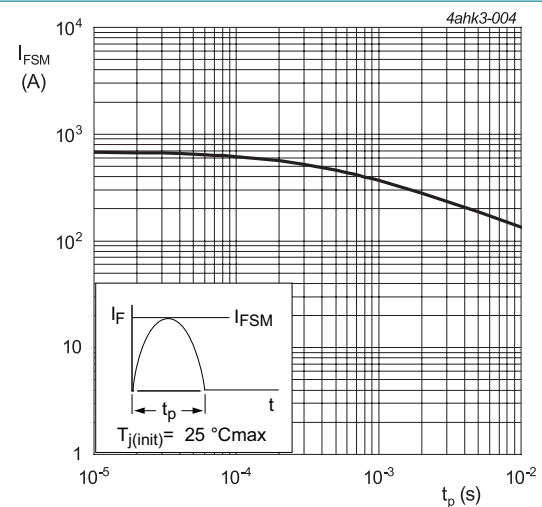


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Notes | Min | Typ | Max | Unit |
|----------------|--|------------------------|---------------------|-----|-----|-----|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | Fig. 5 | | - | - | 1.4 | K/W |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient free air | in free air | [2] | - | 50 | - | K/W |

[2] Device mounted on an FR4 PCB, single-sided copper, tin plated and standard footprint.

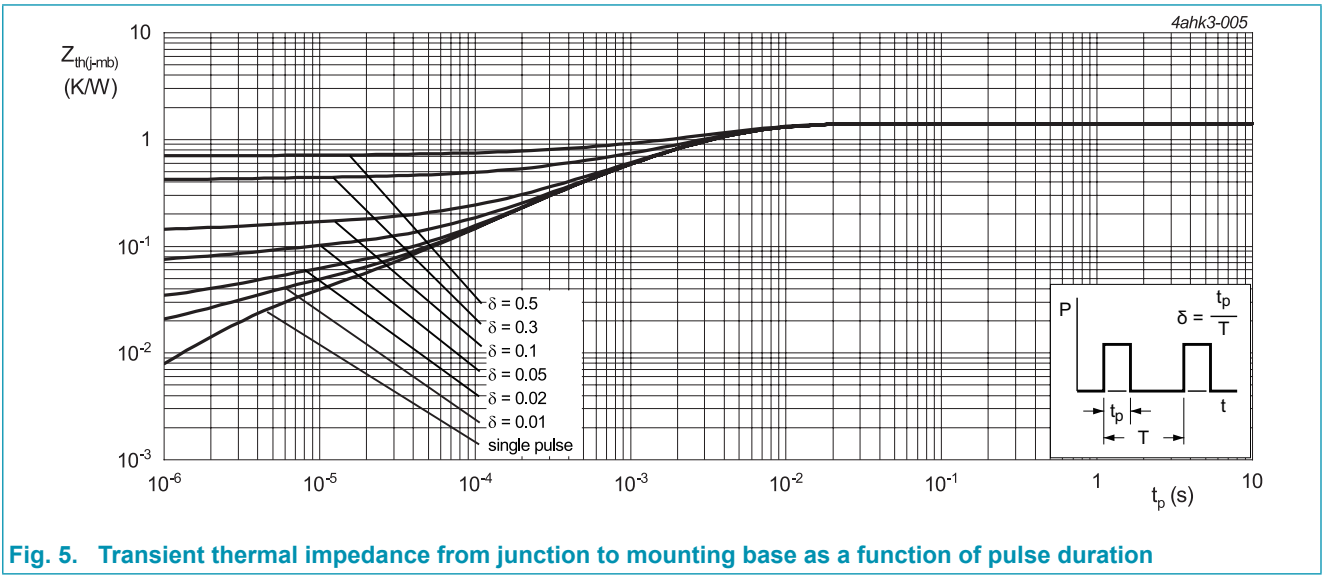
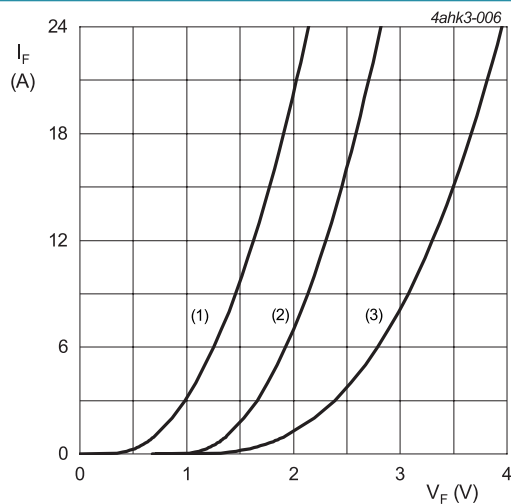


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Notes | Min | Typ | Max | Unit |
|-------------------------|--|--|-------|------|------|------|------|
| Static characteristics | | | | | | | |
| V _F | forward voltage | I _F = 12 A; T _j = 25 °C; Fig. 6 | | - | 2.60 | 3.30 | V |
| | | I _F = 12 A; T _j = 150 °C; Fig. 6 | | - | 1.60 | 2.30 | V |
| I _R | reverse current | V _R = 650 V; T _j = 25 °C | | - | 0.5 | 30 | μA |
| | | V _R = 650 V; T _j = 150 °C | | - | 0.1 | 0.8 | mA |
| Dynamic characteristics | | | | | | | |
| Q _r | reverse charge | I _F = 12 A; V _R = 200 V; dI _F /dt = 200 A/μs; T _j = 25 °C; Fig. 7 | | - | 38 | - | nC |
| | | I _F = 12 A; V _R = 200 V; dI _F /dt = 200 A/μs; T _j = 125 °C; Fig. 7 | | - | 126 | - | nC |
| t _{rr} | reverse recovery time | I _F = 0.5 A; I _R = 1 A; I _{rr} = 0.25 A; T _j = 25 °C | | - | 20 | - | ns |
| | | I _F = 1 A; V _R = 30 V; dI _F /dt = 200 A/μs; T _j = 25 °C; Fig. 7 | | - | 13 | - | ns |
| | | I _F = 12 A; V _R = 200 V; dI _F /dt = 200 A/μs; T _j = 25 °C; Fig. 7 | | - | 30 | - | ns |
| | | I _F = 12 A; V _R = 200 V; dI _F /dt = 200 A/μs; T _j = 125 °C; Fig. 7 | | - | 50 | - | ns |
| I _{RM} | peak reverse recovery current non-repetitive avalanche energy | I _F = 12 A; V _R = 200 V; dI _F /dt = 200 A/μs; T _j = 25 °C; Fig. 7 | | - | 2.6 | - | A |
| | | I _F = 12 A; V _R = 200 V; dI _F /dt = 200 A/μs; T _j = 125 °C; Fig. 7 | | - | 5.1 | - | A |
| E _{as} | non-repetitive avalanche energy | T _{j(init)} = 25 °C | | 10.8 | - | - | mJ |



$V_o = 1.852\text{ V}$; $R_s = 0.0392\text{ }\Omega$

(1) $T_j = 150\text{ °C}$; typical values

(2) $T_j = 150\text{ °C}$; maximum values

(3) $T_j = 25\text{ °C}$; maximum values

Fig. 6. Forward current as a function of forward voltage

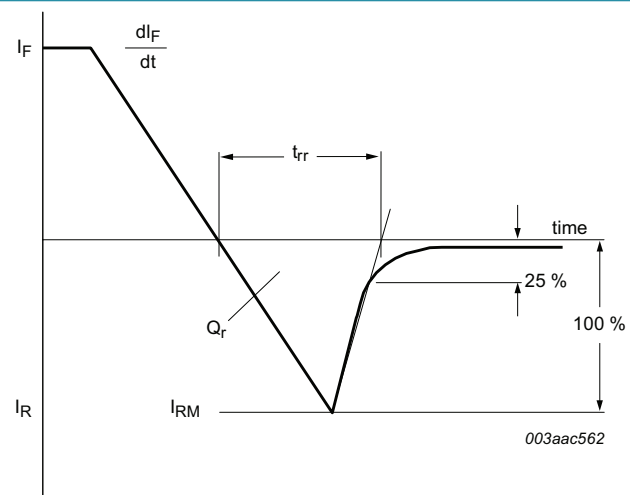


Fig. 7. Reverse recovery definitions; ramp recovery

11. Package outline

Plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)

TO252

GAUGE PLANE 0.508mm

Note:

1. All dimensions do not include mold flash & gate remain and metal protrusion.

| Unit | A | A1 | A2 | b | b1 | b2 | c | D | D1 | D2 | E | E1 | e | e1 | L | L1 |
|------|------|------|------|------|------|------|------|------|------|------|------|------|------|------|------|------|
| min | 2.16 | 0.00 | 0.90 | 0.70 | 0.86 | 1.06 | 0.46 | 5.97 | 5.05 | 0.98 | 6.45 | 5.20 | 2.30 | 4.60 | 2.60 | 1.25 |
| max | 2.41 | 0.10 | 1.10 | 0.90 | 1.11 | 1.32 | 0.58 | 6.22 | 5.35 | 1.18 | 6.75 | 5.40 | | | 2.90 | 1.65 |

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| Document status [1][2] | Product status [3] | Definition |
|--------------------------------|--------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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